

## IGBT

Low  $V_{CE(sat)}$  IGBT in TRENCHSTOP™ 5 technology

## IGW30N65L5

650V IGBT Low  $V_{CE(sat)}$  series fifth generation

Data sheet

Industrial Power Control

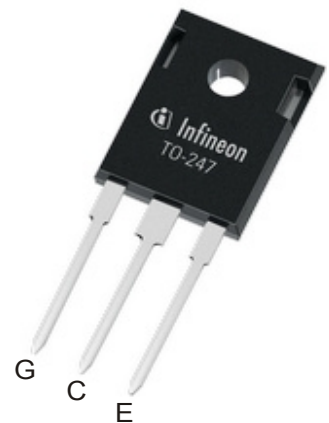
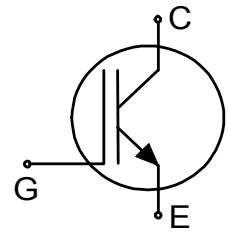
Low  $V_{CE(sat)}$  series fifth generation

Low  $V_{CE(sat)}$  IGBT in TRENCHSTOP™ 5 technology

#### Features and Benefits:

Low  $V_{CE(sat)}$  L5 technology offering

- Very low collector-emitter saturation voltage  $V_{CEsat}$
- Best-in-Class tradeoff between conduction and switching losses
- 650V breakdown voltage
- Low gate charge  $Q_G$
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating
- RoHS compliant
- Complete product spectrum and PSpice models:  
<http://www.infineon.com/igbt/>



#### Applications:

- Uninterruptible power supplies
- Solar photovoltaic inverters
- Welding machines

#### Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



#### Key Performance and Package Parameters

Type	$V_{CE}$	$I_C$	$V_{CEsat}, T_{vj}=25^{\circ}C$	$T_{vjmax}$	Marking	Package
IGW30N65L5	650V	30A	1.05V	175°C	G30EL5	PG-TO247-3